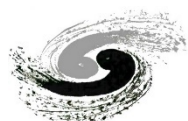


# A Beam Test Facility for High Current Photoinjector and its Key Technologies Development at IHEP

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*Chinese Academy of Sciences*

ERL2017, 21 June 2017, Cern

# Outline

- PAPS introduction
- A Beam Test Facility for High Current Photoinjector
- Related Key Technologies Development
- Future plan
- Summary and Outlook

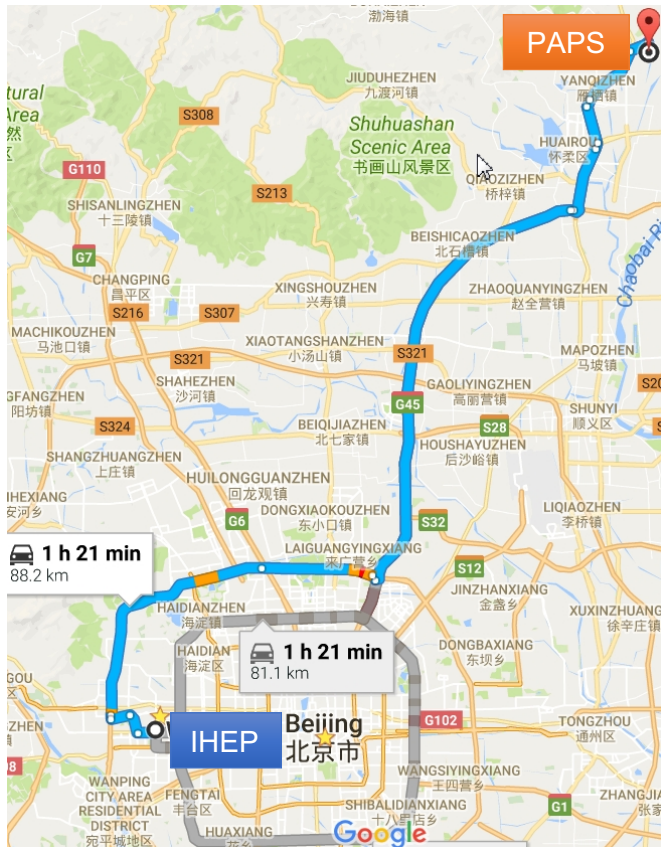
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# PAPS Introduction

**P**latform of **A**dvanced **P**hoton **S**ource Technology R&D,  
Huairou Science Park, Huairou, Beijing

HEPS



Construction: 2017.5 – 2020.6  
Ground Breaking: May 31, 2017

# PAPS Introduction

## Cryogenic system

**2.5kW@4.5K/300W@2K**

## 800L/h liquidation

- 100W for 3 vertical test stands
- 100W for 2 horizontal module test stands
- 100W for beam test system

## X-ray system

- Advanced X-ray related technologies R&D



## 4500 m<sup>2</sup> SRF lab

**Mission:** World-leading SRF Lab for future Superconducting Accelerator Projects and SRF Frontier R&D

- Three vertical test stands each with four cavities
- Coupler conditioning stands for eight couplers
- 30 m-long clean room
- 36 m-long module assembly zone
- Two horizontal module test stands (12m module)

## Beam test system

- Beam test based on superconducting module
- High power conditioning (High efficiency klystron)
- High current photoinjector R&D

## Magnet system

- Precision machining for HEPS magnets

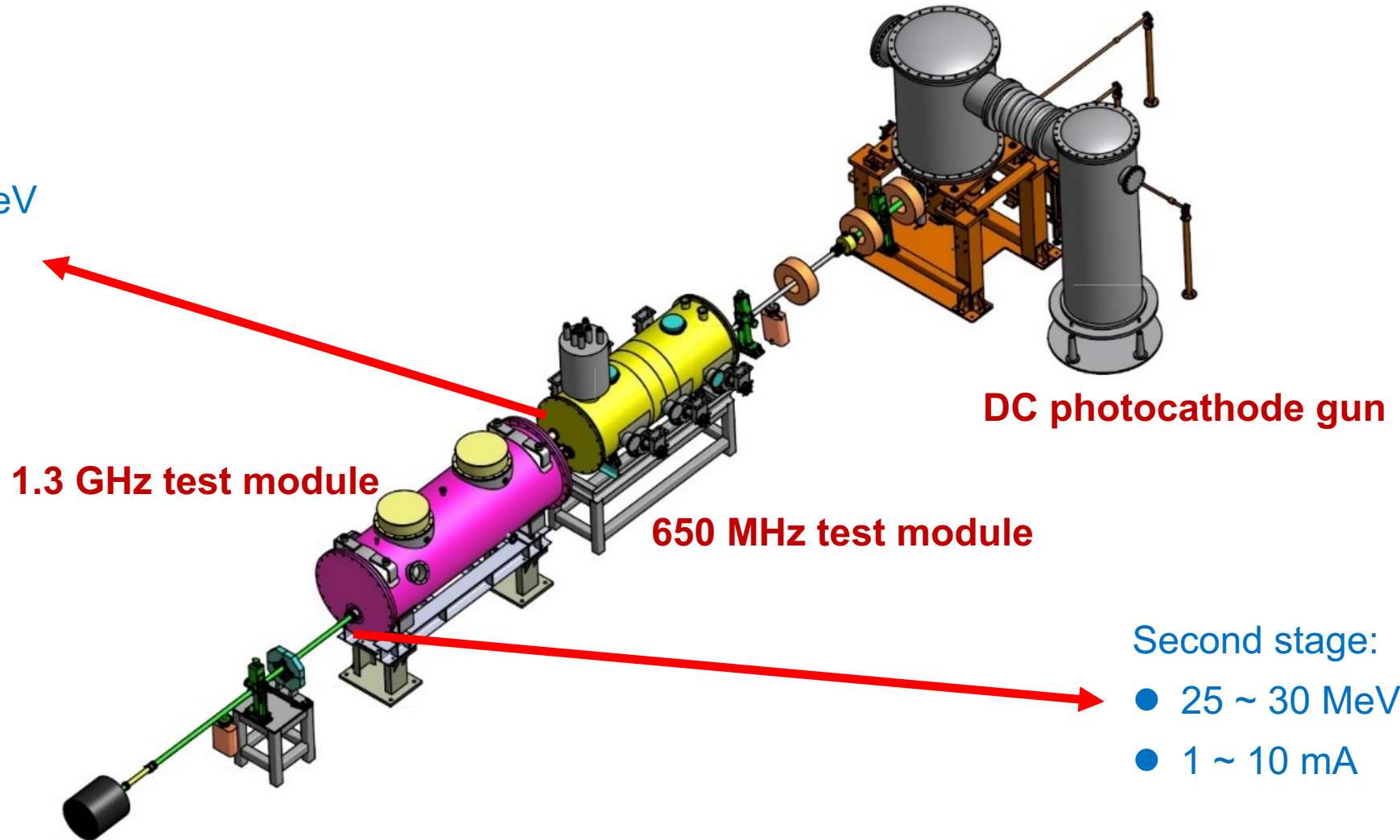
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# PAPS Beam Test System

First stage:

- 10 ~ 15 MeV
- 1 ~ 10 mA



Second stage:

- 25 ~ 30 MeV
- 1 ~ 10 mA

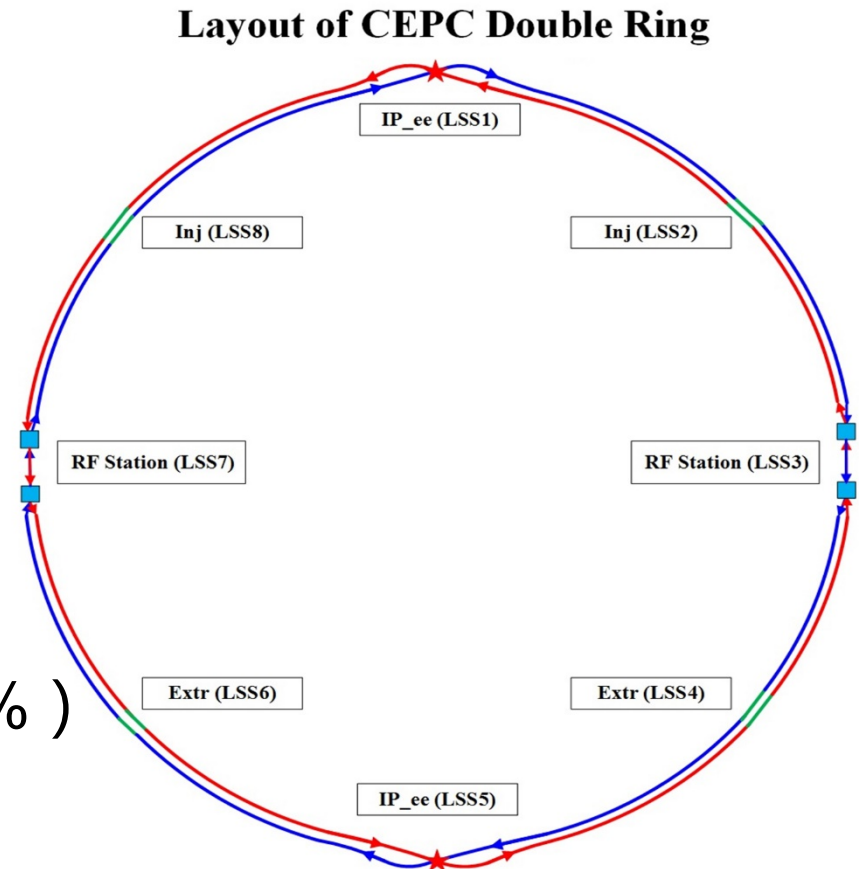
# PAPS Beam Test System

Why is 650MHz SRF ?

- The R&D of CEPC (Circular Electron Positron Collider)
- Circumference: 100 km
- Ring type: Double Ring (*baseline*)
- SRF System: 650MHz in the Main Ring of CEPC

Several key technologies R&D already started

- 650MHz High-Q SRF Cavity
- High power ( 300kW CW ) 650MHz Input Coupler
- High power 650MHz Klystron ( 800kW, efficiency $\geq$ 75% )
- 650MHz Cryomodule (650 MHz 6 x 2-cell Cavities)
- 1.6MW PSM Power Supply for Klystron



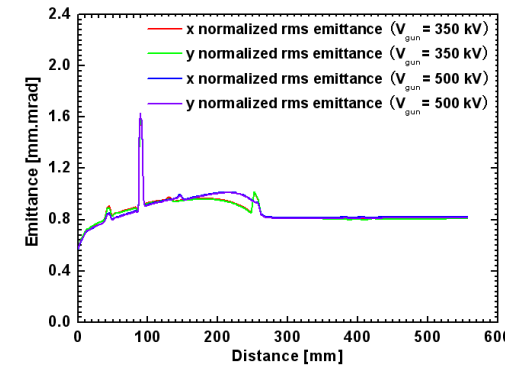
# PAPS Beam Test System

## Preliminary beam dynamics study

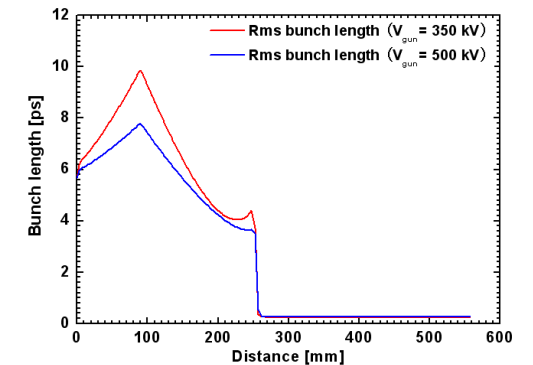
- From gun to exit of 650MHz cryomodule
- To be continued.....

### Input parameters of simulation

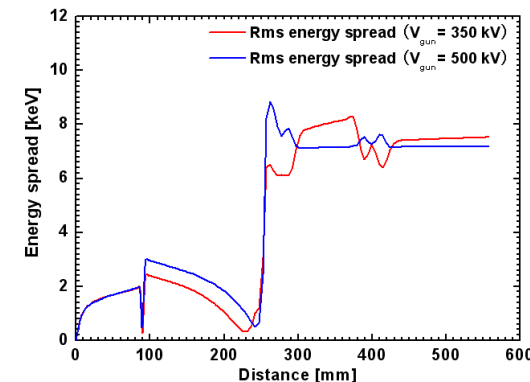
| Parameter                      | Value                                               |
|--------------------------------|-----------------------------------------------------|
| DC-gun voltage                 | 350 kV / 500 kV                                     |
| Beam current                   | 10mA                                                |
| Bunch repetition frequency     | 650MHz                                              |
| Bunch charge                   | 15.4pC                                              |
| Beam transverse distribution   | round and uniform                                   |
| Beam longitudinal distribution | beer can with 18 ps flat top and 2ps rise/fall time |
| NC buncher voltage             | 82.8 kV/ 111.6kV                                    |
| Gradient for SC cavity         | 18MV/m                                              |



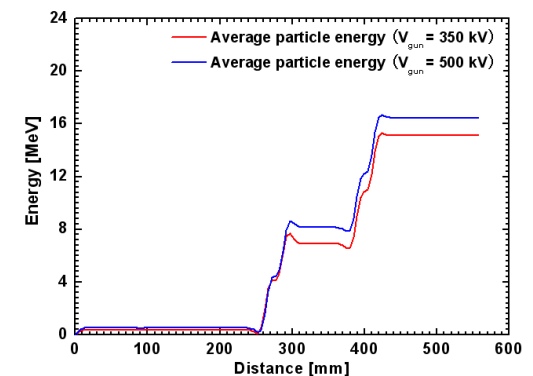
Emittance



Bunch length



Energy spread



Energy

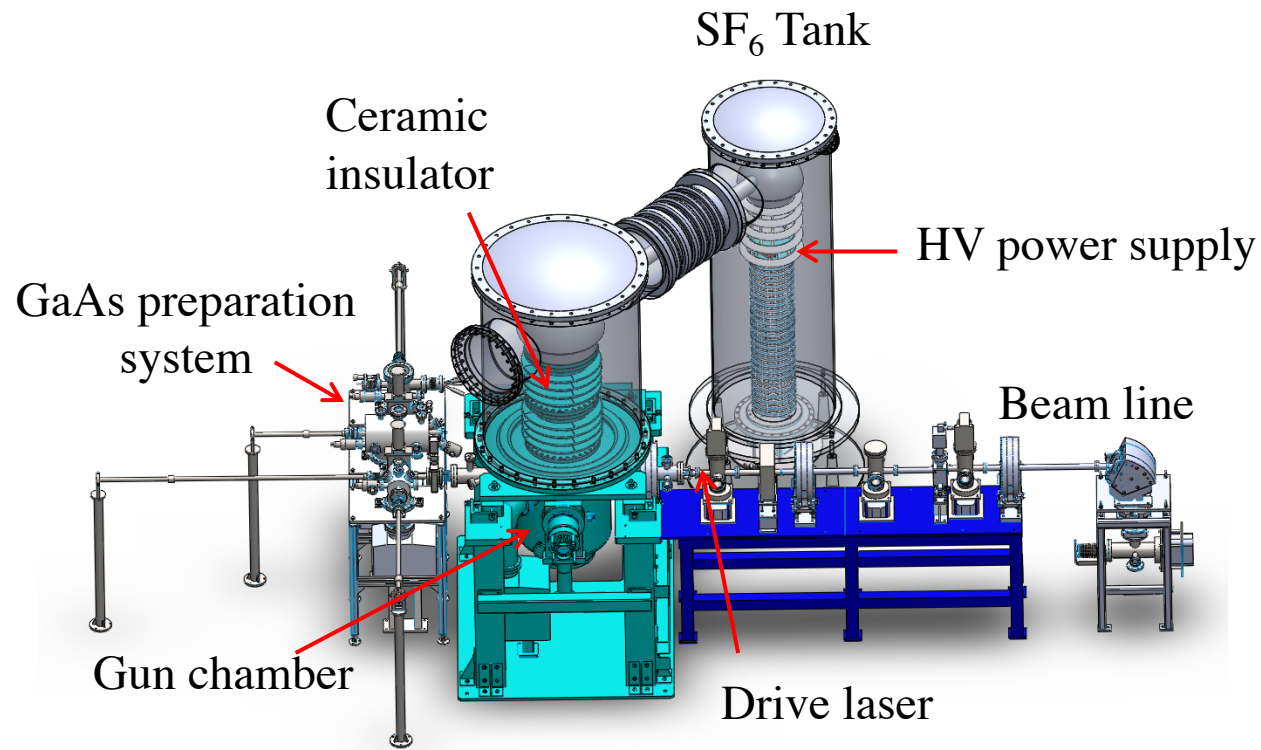
# Outline

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- [Related Key Technologies Development](#)
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# Related Key Technologies Development (1)

## A photocathode DC-Gun R&D

- Design and parameters



Layout of Photocathode DC-Gun

| Parameter       | Value             |
|-----------------|-------------------|
| HV              | 350 ~ 500 kV      |
| Cathode         | GaAs:Cs           |
| QE              | 5-7%(initial), 1% |
| Driven laser    | 2.3W, 530nm       |
| Repetition rate | 100MHz, 1.3GHz*   |
| Nor. emittance  | (1~2)mm.mrad      |
| Bunch length    | 20ps              |
| Beam current    | (1~10) mA         |

\*Two operation modes:

1). 100MHz-7.7mA-77pC, 2)1300MHz-10mA-7.7pC

# Related Key Technologies Development (1)

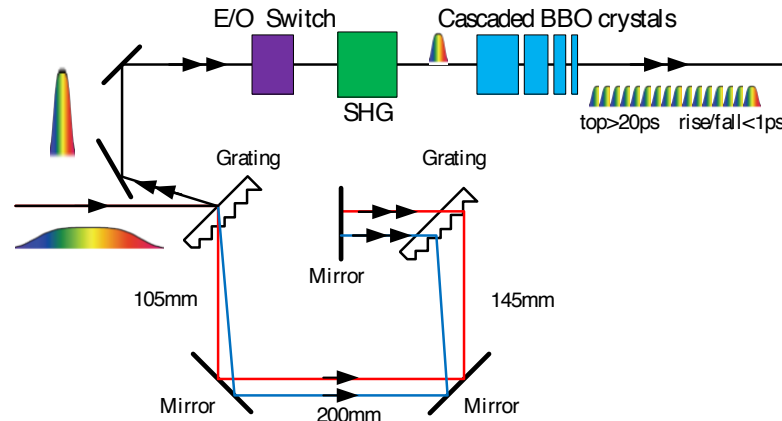
## A photocathode DC-Gun R&D

- Construction: Laser system

1. Two laser oscillators are working at 1.3GHz and 100MHz respectively
2. 100MHz and 1.3GHz oscillators are integrated into one laser system with a 2x2 fiber coupler
3. The green laser output power after SHG crystal is more than **5W**
4. A set of four a-BBO crystals is used as longitudinal pulse shaper stacking an input pulse to **>20ps**

| Parameters              | 1st mode | 2nd mode |
|-------------------------|----------|----------|
| Electron bunch charge   | 77pC     | 7.7pC    |
| Pulse energy at cathode | 18nJ     | 1.8nJ    |
| Pulse repetition rate   | 100MHz   | 1.3GHz   |
| Power at cathode        | 1.8W     | 2.3W     |
| Pulse length (flattop)  | 20-30ps  | 20-30ps  |

Requirements for two operation modes



Laser pulse modification and shaping

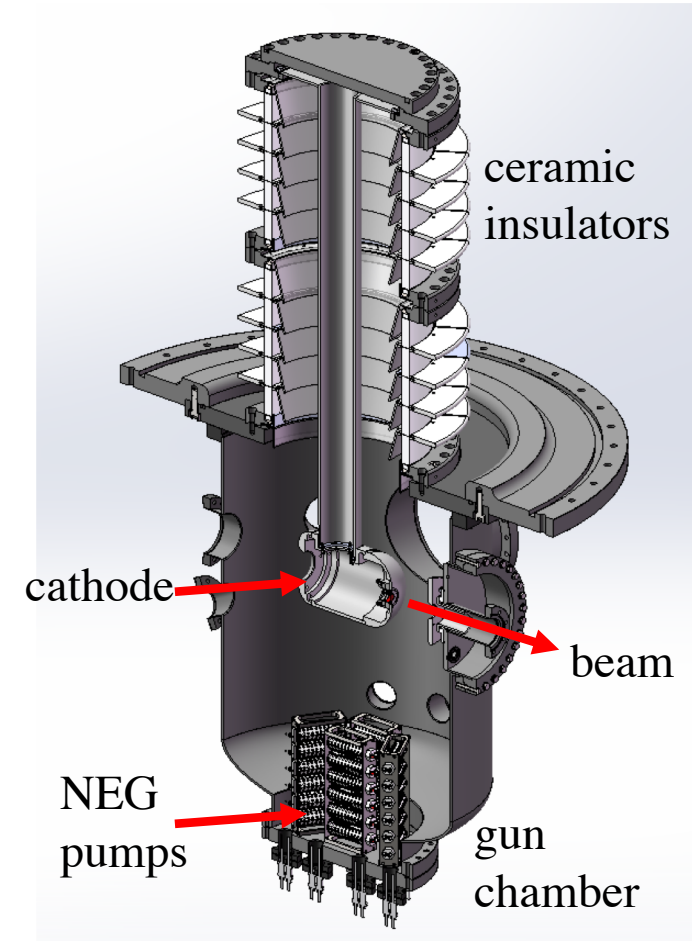
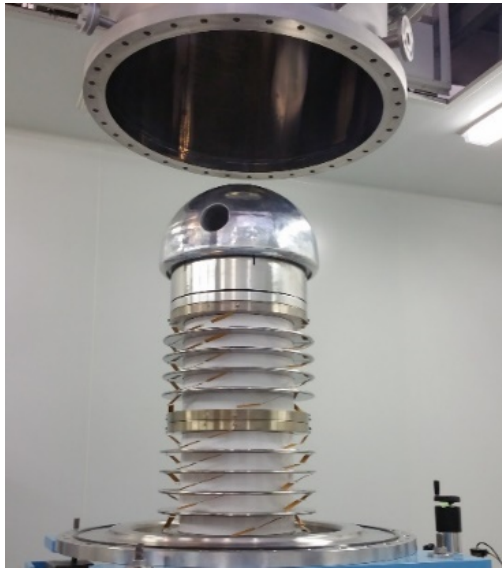


Laser system for photocathode

# Related Key Technologies Development (1)

## A photocathode DC-Gun R&D

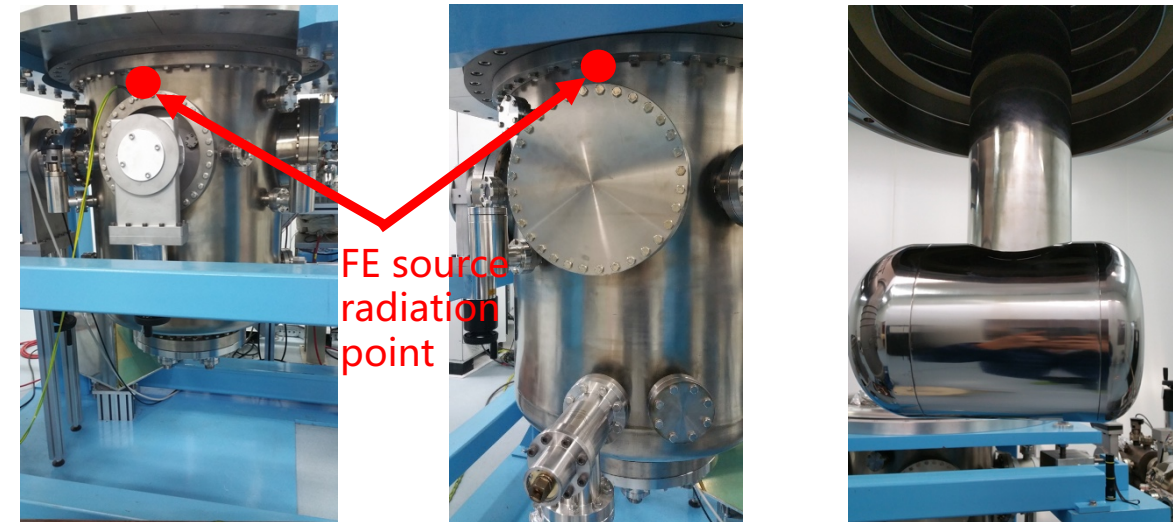
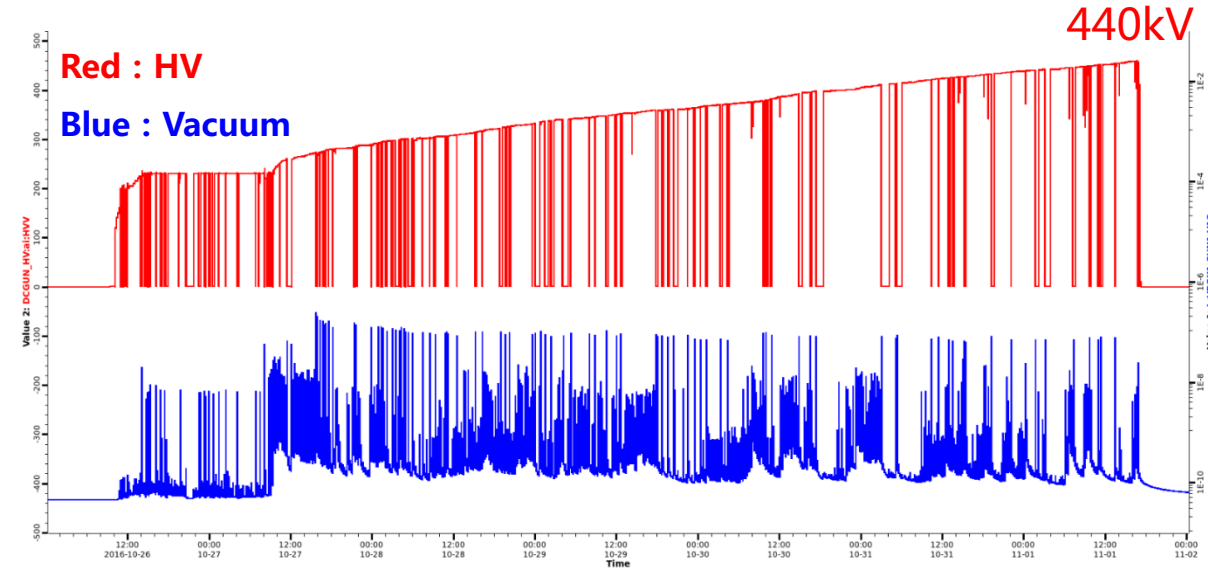
- Construction: ceramics, gun, power supply, beam line.....
  1. Construction of each component is done
  2. Vacuum in the gun achieves  $6 \times 10^{-10} \text{Pa}$
  3. Pressurized insulating gas: SF<sub>6</sub>



# Related Key Technologies Development (1)

## A photocathode DC-Gun R&D

- High voltage conditioning
  1. The pressure of SF6 in the pressurized tank: 2.5atm
  2. The vacuum interlock level is  $4 \times 10^{-6}$ Pa
  3. After around 140 hours conditioning, HV reached up to **440kV** that means a HV between cathode and anode is around **431kV** (5000MΩ/5100MΩ)
  4. Then a huge radiation dose caused by field emission was found at one point of gun chamber. There is still a big dose even though reduce the HV to 250kV.
  5. Open the gun chamber and repolish the cathode to remove FE source, then recover the vacuum
  6. Re-conditioning up to **370kV** (HV between cathode and anode is **362kV**) without obvious dose
  7. Next, beam operation @**350kV**



# Related Key Technologies Development (1)

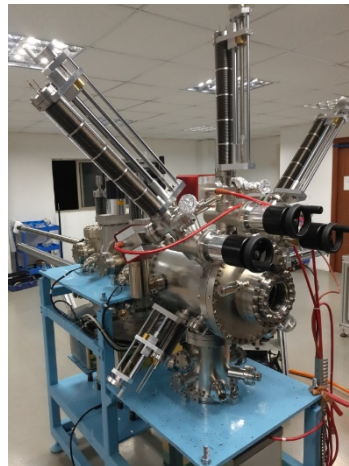
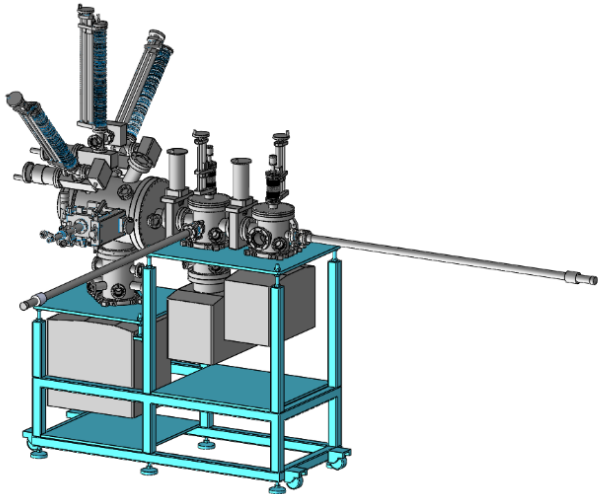
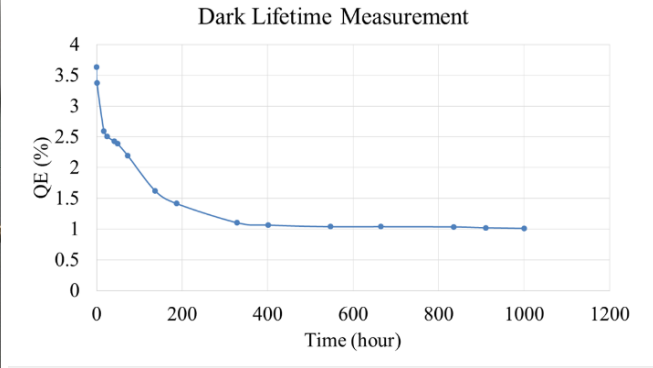
## A photocathode DC-Gun R&D

- Photocathode development

1. A GaAs photocathode system was built up at first
2. Obtained a QE of ~10% after Cs/O activation
3. Dark lifetime can keep 1000hr with  $QE \geq 1\%$
4. In recent, a  $K_2CsSb$  photocathode system was set up, growth experiment just started



GaAs photocathode system



$K_2CsSb$  photocathode system



Mo substrate

# Related Key Technologies Development (2)

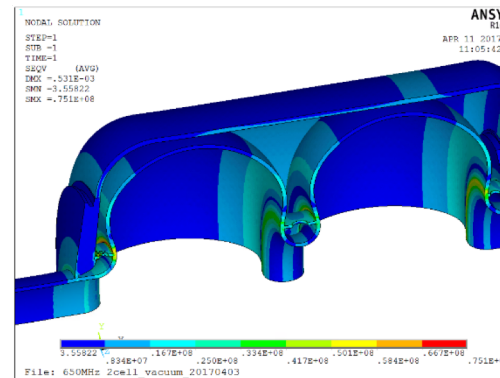
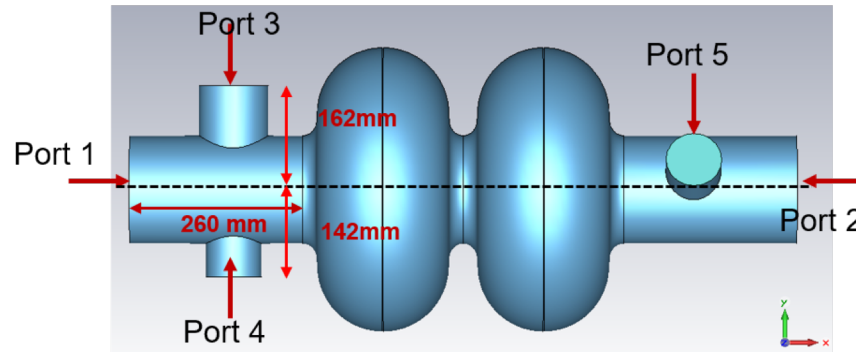
## 650MHz SRF cavity and Cryomodule

- 650MHz SRF cavity design

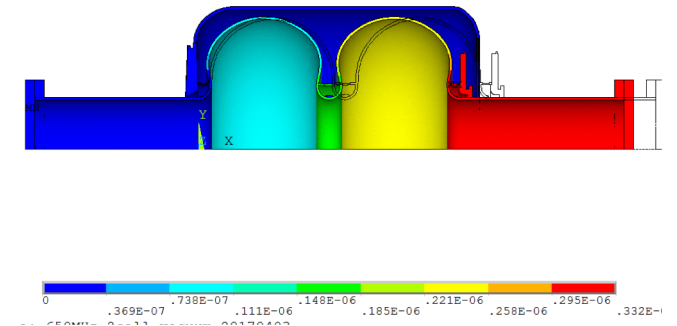
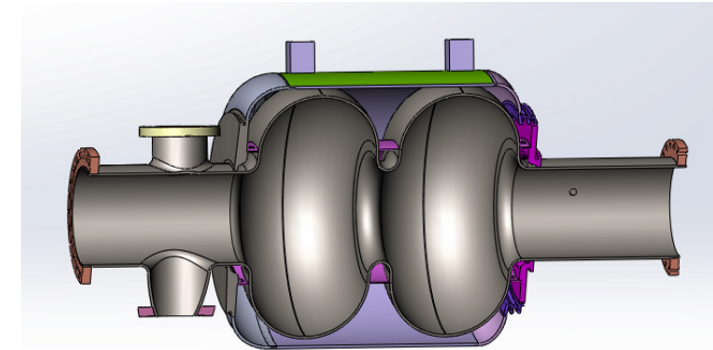
| Parameters                | Value |
|---------------------------|-------|
| $R/Q$ ( $\Omega$ )        | 213   |
| $G$ ( $\Omega$ )          | 284   |
| $E_p/E_{acc}$             | 2.4   |
| $B_p/E_{acc}$ [mT/(MV/m)] | 4.2   |

|        | $P$ (W) ( $U = 1$ J) | $Q_e$   |
|--------|----------------------|---------|
| Port 1 | 0.001867             | 2.19E12 |
| Port 2 | 0.001352             | 3.02E12 |
| Port 3 | 0.005441             | 7.51E11 |
| Port 4 | 0.003435             | 1.19E12 |
| Port 5 | 0.003320             | 1.23E12 |

$Q_e$  (all ports) :  $2.65E+11$ . If  $Q_0 = 4E10$  ,  
then  $Q_0$  (measured) decrease to  $3.48E10$ .



df/dp and stress



LFD

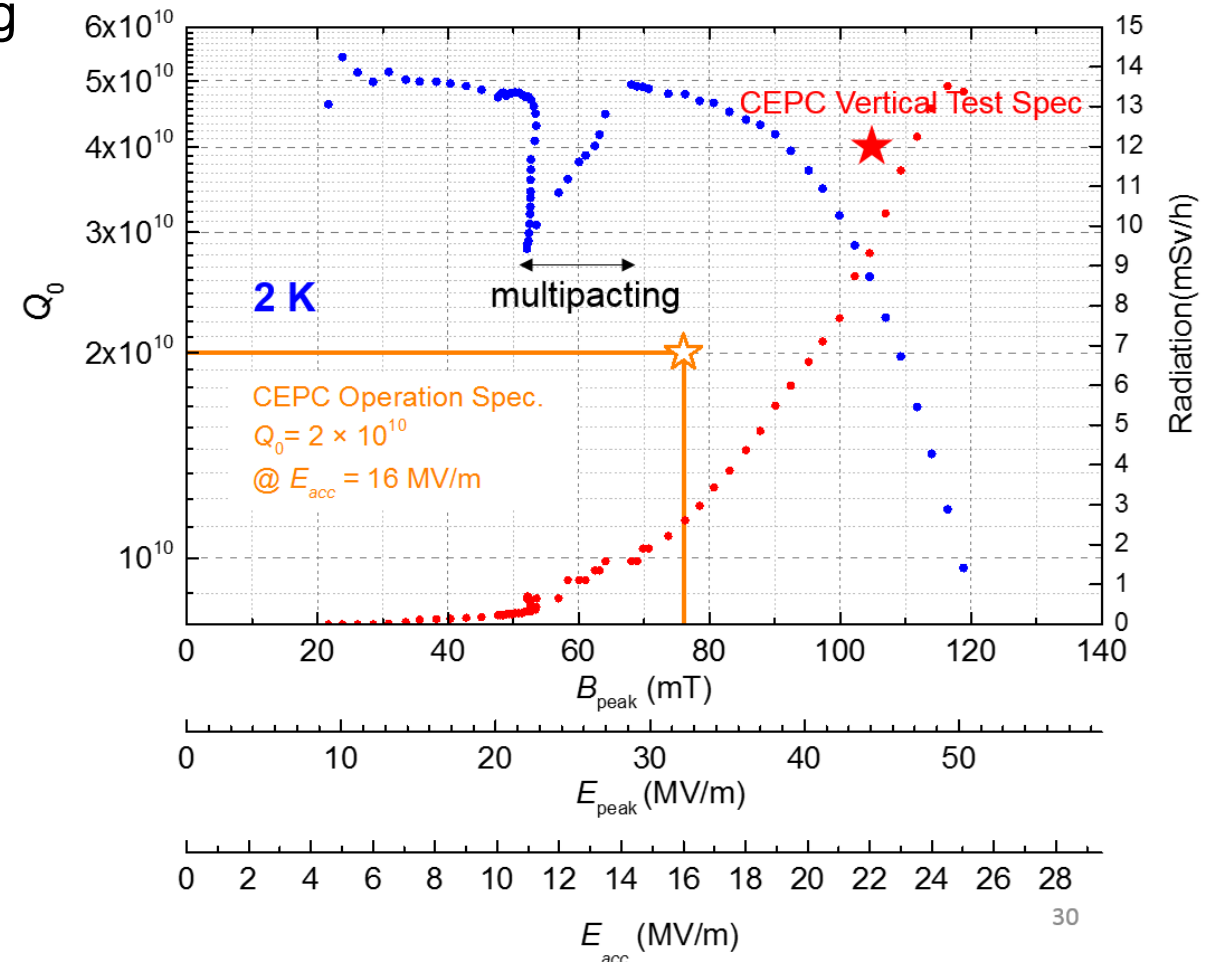
# Related Key Technologies Development (2)

## 650MHz SRF cavity and Cryomodule

- 650 MHz Single Cell Cavity Test before N-doping



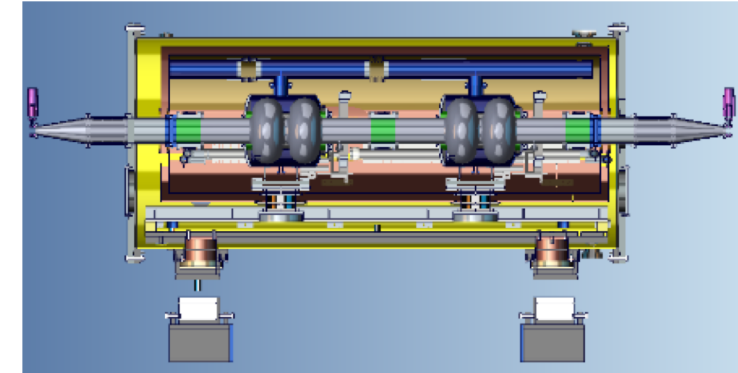
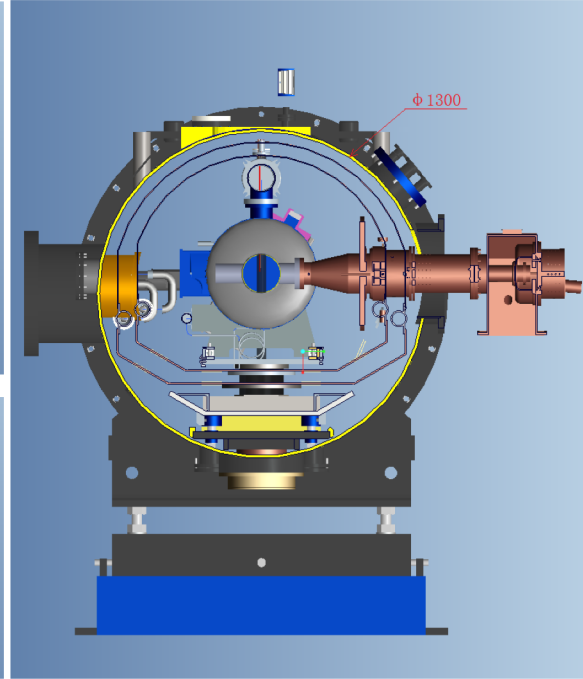
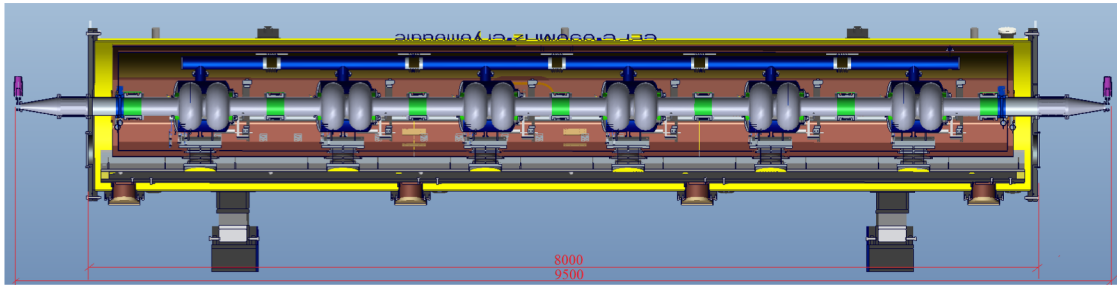
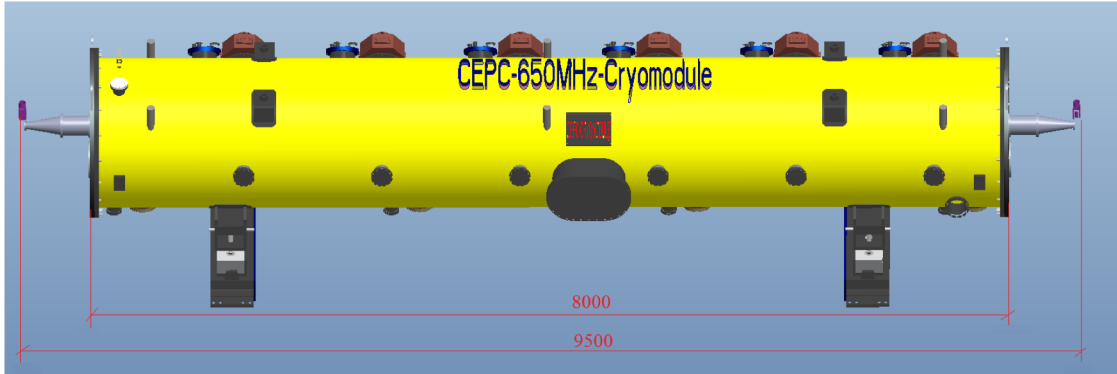
- Fine grain, BCP + 120 C bake 48 h
- $Q_0 = 4 \times 10^{10}$  @  $E_{acc} = 19.4 \text{ MV/m}$
- Next step: cavity N-infusion; N-doping + EP



# Related Key Technologies Development (2)

## 650MHz SRF cavity and Cryomodule

- CEPC full scale Prototype Cryomodule design and small Test Cryomodule for PAPS



PAPS small Test Cryomodule  
with 650MHz 2 x 2-cell  
cavities

CEPC full scale prototype cryomodule with 650 MHz 6 x 2-cell cavities

# Related Key Technologies Development (3)

## 650MHz High Efficiency Klystron (CW 800kW and efficiency $\geq$ 75%)

- R&D plan

- 2017-2019 (Prototype 1)

- Five fundamental cavities and One 2<sup>nd</sup> harmonic cavity
- Design is already done and soon the fabrication will be started
- Plan to finish assembling before December 2018
- Installed on PAPS (beam test system) before June 2019
- 600kW with 65% efficiency operation at PAPS

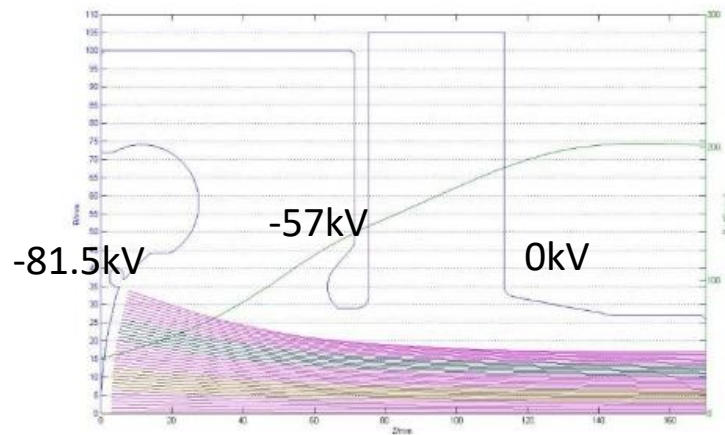
- 2019-2021 (Prototype 2)

- First option: Five fundamental cavities, One 2<sup>nd</sup> harmonic cavity and One 3<sup>rd</sup> harmonic cavity
- Second option: 8/9 cavities by using BAC method or other methods
- Finally, achieve 800kW output with efficiency  $\geq$  75%

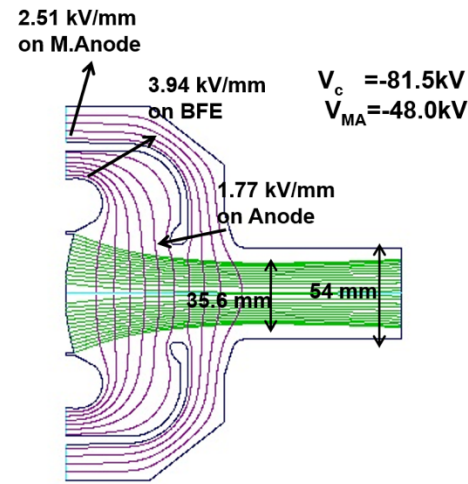
# Related Key Technologies Development (3)

650MHz High Efficiency Klystron (CW 800kW and efficiency $\geq$ 75%)

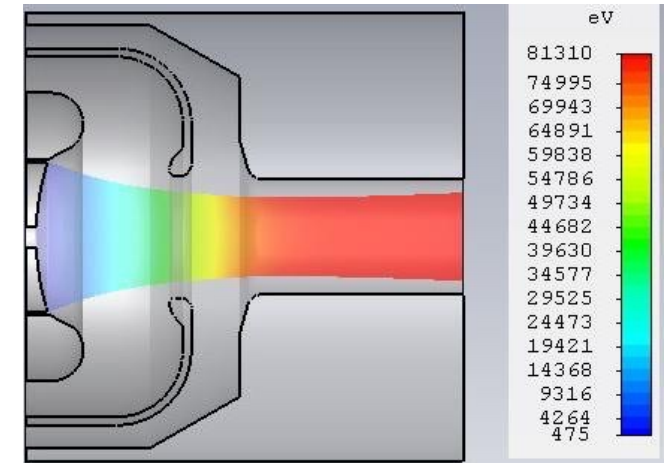
- Prototype 1: Electron gun simulation



EGUN



DGUN



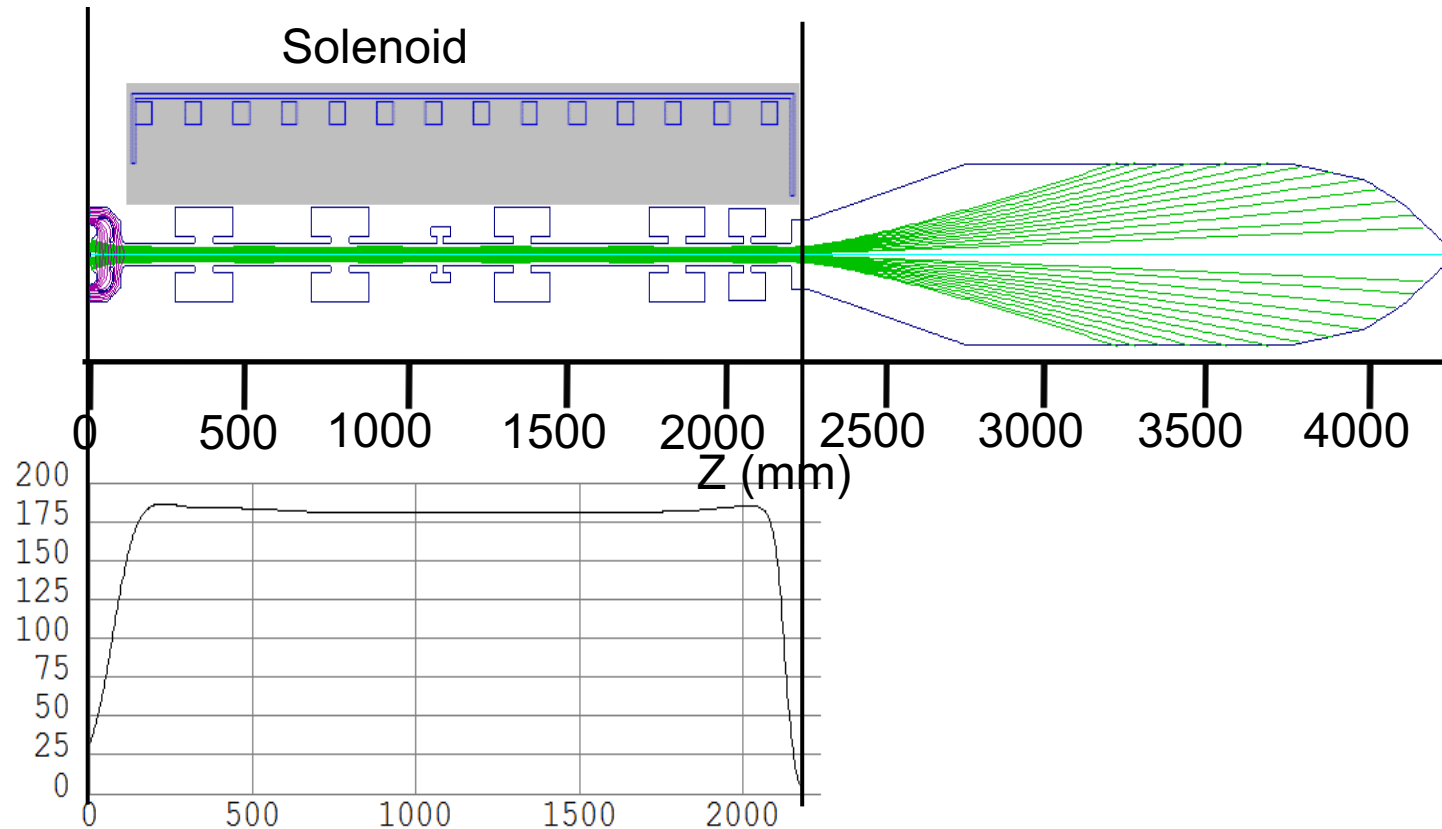
CST

| Type                         | DGUN  | EGUN  | CST   |
|------------------------------|-------|-------|-------|
| Current(A)                   | 15.12 | 14.88 | 14.88 |
| Beam DIA(mm)                 | 17.8  | 17.7  | 17.7  |
| Perveance( $\mu A/V^{3/2}$ ) | 1.43  | 1.41  | 1.41  |

# Related Key Technologies Development (3)

650MHz High Efficiency Klystron (CW 800kW and efficiency $\geq 75\%$ )

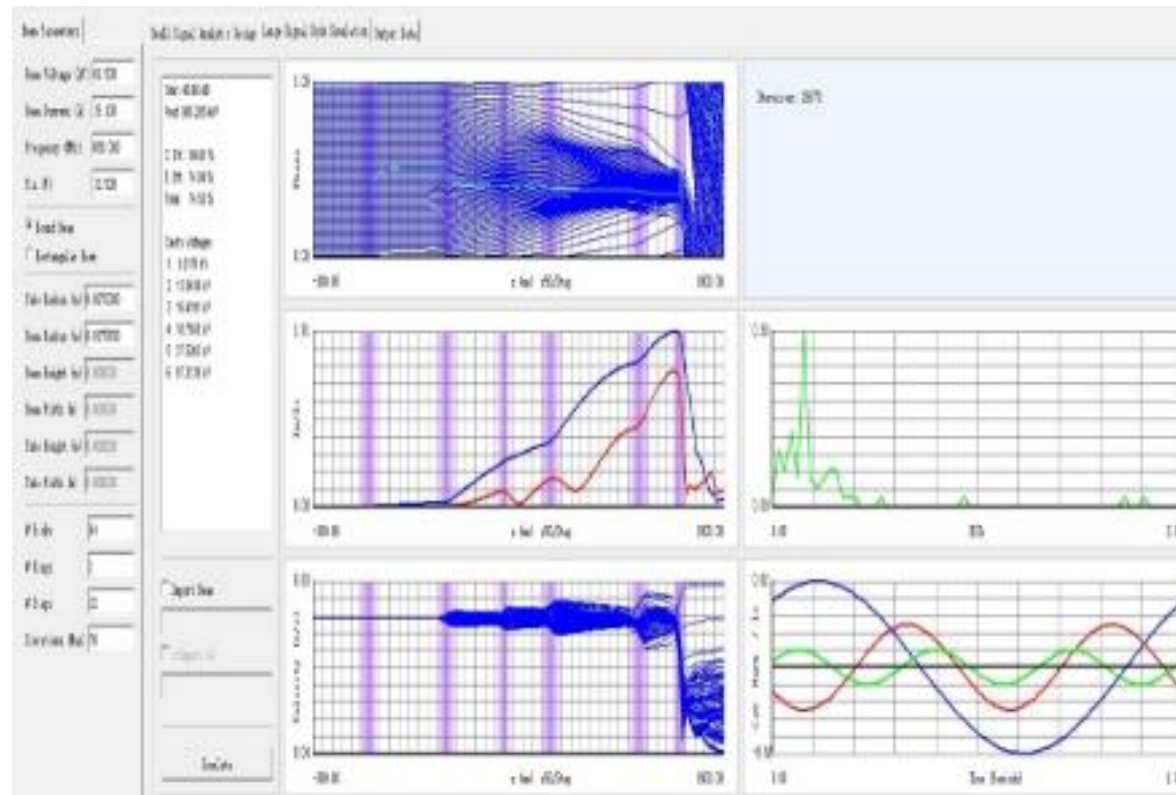
- Prototype 1: Beam trajectory



# Related Key Technologies Development (3)

650MHz High Efficiency Klystron (CW 800kW and efficiency $\geq$ 75%)

- Prototype 1: AJ disk 1d simulation result shows 74.55% efficiency



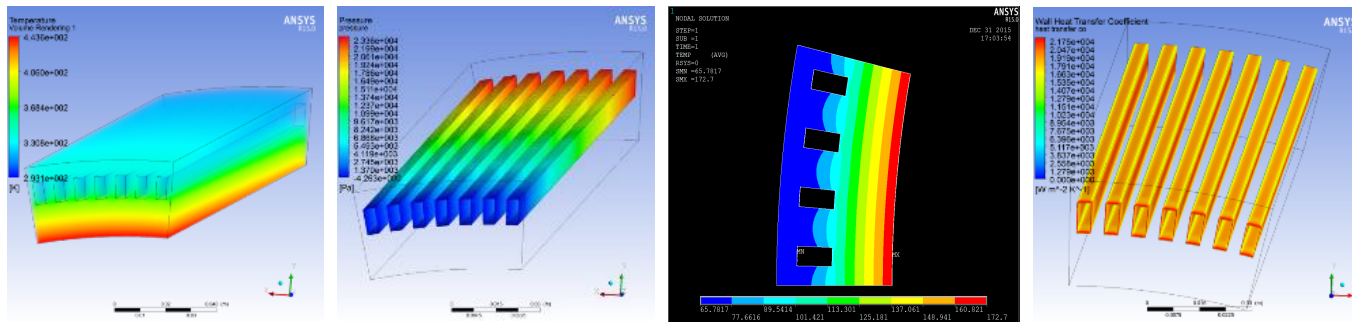
AJ disk design

# Related Key Technologies Development (3)

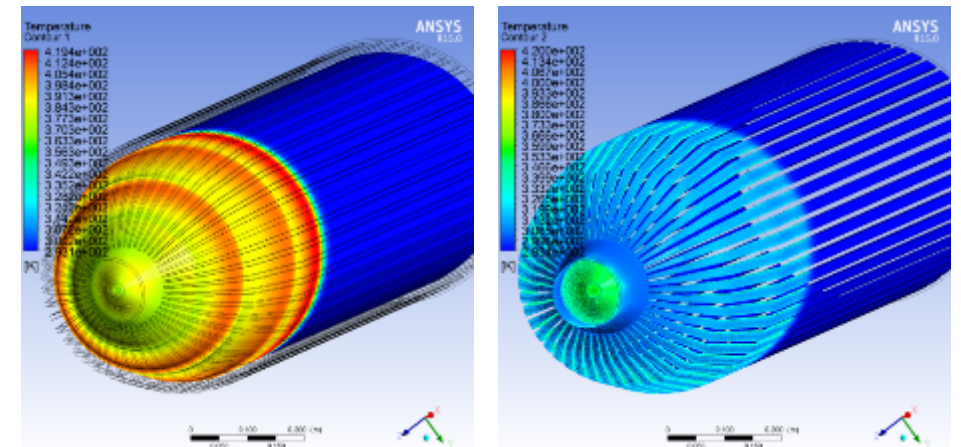
650MHz High Efficiency Klystron (CW 800kW and efficiency $\geq$ 75%)

- Prototype 1: Full power (~1.23MW) collector design

| Groove number | Groove dimensions(a:b) | Total water flow rate | Water pressure loss for smooth surface |
|---------------|------------------------|-----------------------|----------------------------------------|
| 180           | 1:2                    | 1400kg/min            | 2.34E+4 Pa                             |



Temperature and water pressure loss



Temperature on inner surface of copper domain and water domain

# Related Key Technologies Development (4)

## PSM (Pulse Step Modulation) Power Supply

- In ADS project, a **80kV/18A** PSM power supply was developed for 325MHz 600kW klystron at IHEP
- In PAPS, a **120kV/16A** PSM power supply will be developed for 650MHz 800kW klystron



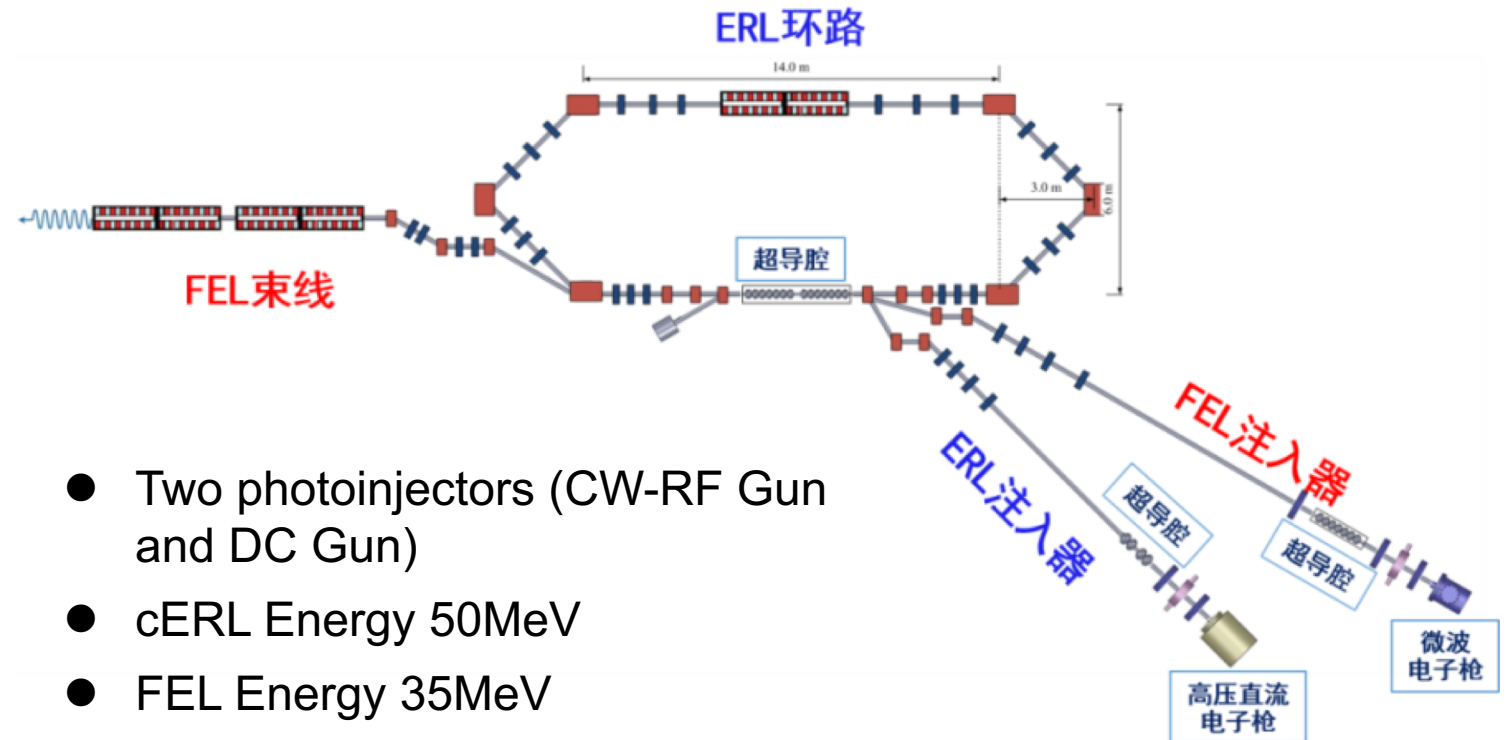
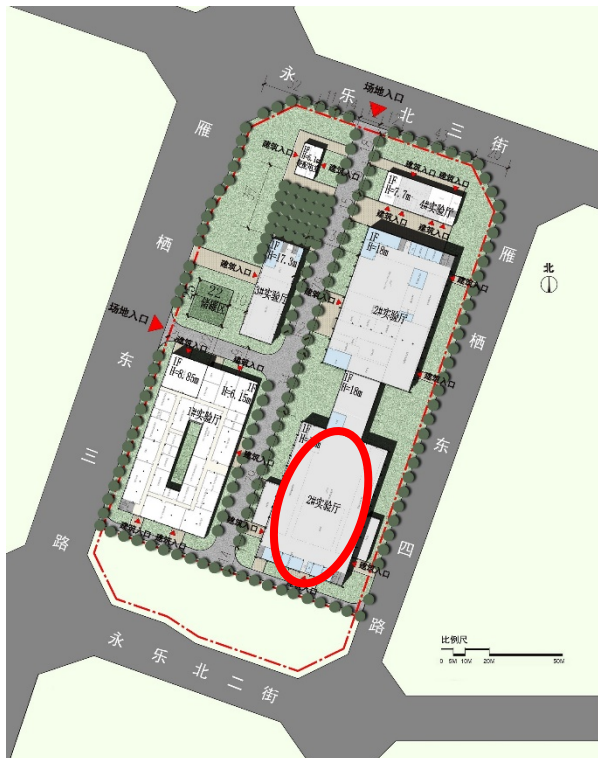
ADS 80kV/18A PSM Power Supply

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# Future Plan

- First, construction and beam operation of beam test system at PAPS (2017.5-2020.6)
- After 2020, the hall for Magnet system will be free up. A compact test facility towards one machine, two purposes: using a common SC linac for XFEL and ERL simultaneously now is proposed at IHEP



- Two photoinjectors (CW-RF Gun and DC Gun)
- cERL Energy 50MeV
- FEL Energy 35MeV

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# Summary and Outlook

- A new project PAPS has been supported by Beijing Government from 2017.5-2020.6
- A beam test system based on photocathode DC Gun and 650MHz SRF will be constructed at PAPS
- Several related key technologies already been developed in recent years at IHEP, including photocathode DC Gun, 650MHz SRF cavities, High power high efficiency klystrons and its PSM power supply.....

*Thank you!*